

0910 - 150M

150 Watts - 48 Volts, 150μs, 5% Radar 890 - 1000 MHz

GENERAL DESCRIPTION

The 0910-150M is an internally matched, COMMON BASE transistor capable of providing 150 Watts of pulsed RF output power at 150 μs pulse width, 5% duty factor across the band 890 to 1000 MHz. This hermetically solder-sealed transistor is specifically designed for P-Band radar applications. It utilizes gold metallization to provide high reliability.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 400 Watts

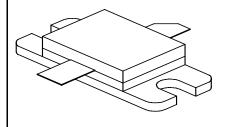
Maximum Voltage and Current

BVces Collector to Emitter Voltage 65 Volts
BVebo Emitter to Base Voltage 3.5 Volts
Ic Collector Current 12 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 200^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$

CASE OUTLINE 55KT, STYLE 1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pg ¶c Pd Rl VSWR¹ VSWRs	Power Out Power Gain Collector Efficiency Pulse Droop Input Return loss Load Mismatch Tolerance Load Mismatch - Stability	Freq = 890 – 1000 MHz Vcc = 48 Volts Pin = 23 Watts Pulse Width = 150µs Duty Factor = 5%	150 8.1 40	8.5 45	210 0.5 3:1 2:1	Watts dB % dB dB

Note 1: Pulse condition of 150µsec, 5%.

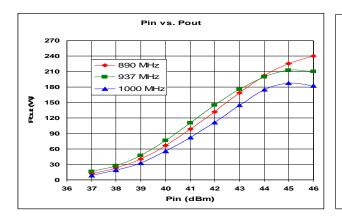
Bvces Ices	Collector to Emitter Breakdown Collector to Emitter Leakage	Ic = 10 mA Vce = 50 Volts	65	10	Volts mA
Iebo	Emitter to Base Leakage	Vebo = 2.5 Volts		5.0	mA
$\mathbf{\theta}\mathbf{j}\mathbf{c}^1$	Thermal Resistance	Rated Pulse Condition		0.48	°C/W

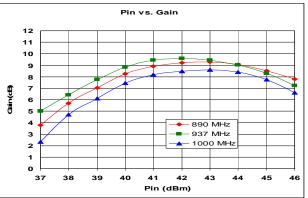
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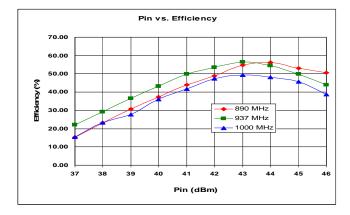


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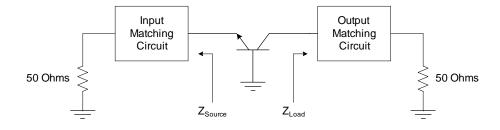
Performance Curves –







Impedance Information



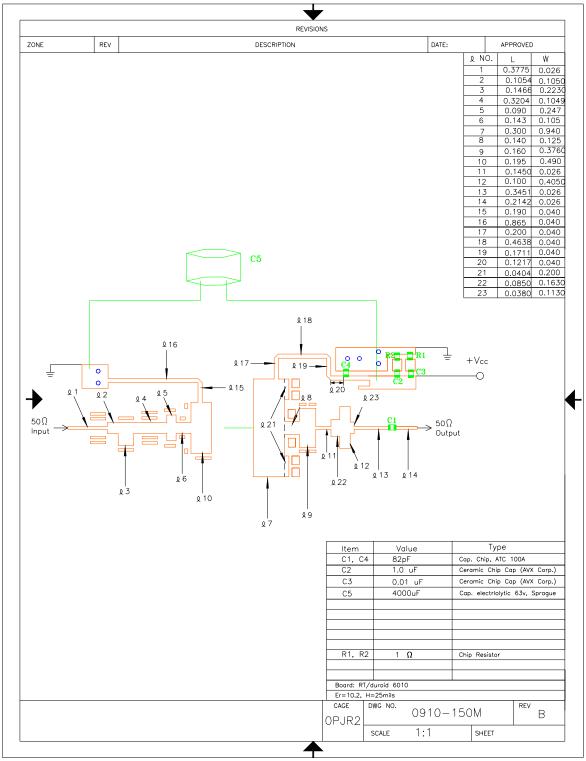
Frequencies (MHz)	$Z_{\scriptscriptstyle Source}(\Omega)$	$Z_{Load}(\Omega)^{2}$
890	4.0 - j4.2	1.85 - j3.2
937	4.0 - j3.5	1.97 - j3.0
1000	4.1 - j2.5	2.1 - j3.0

Note 2: Z_{Load} exclusive of C1 and C4 on the test circuit



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Test Circuit





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Case Outline

